

## **isc Silicon NPN Power Transistor**

# BU508AF

## DESCRIPTION

- Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 700V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

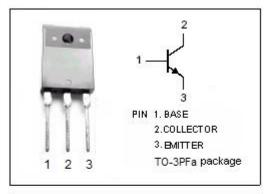
## **APPLICATIONS**

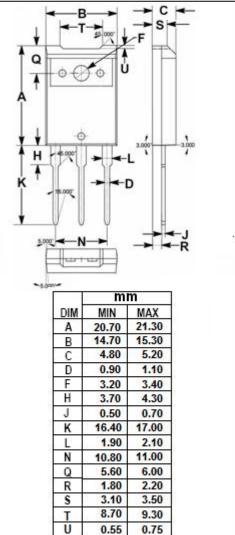
Designed for use in horizontal deflection circuits of color TV receivers.

ABSOLUTE WAXIMUWI KATINGS(Ta=25 C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CES</sub>	Collector- Emitter Voltage(V <sub>BE</sub> = 0)	1500	v				
V <sub>CEO</sub>	Collector-Emitter Voltage	700	v				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
Ic	Collector Current- Continuous	8	А				
I <sub>CM</sub>	Collector Current-Peak	15	А				
I <sub>B</sub>	Base Current- Continuous	4	А				
I <sub>BM</sub>	Base Current-Peak	6	А				
Pc	Collector Power Dissipation @ $T_c$ =25 °C	60	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C				
	1	1					

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.5	





isc website: <u>www.iscsemi.com</u>



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## ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	700			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4.5A; I <sub>B</sub> = 2.0A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0 V <sub>CE</sub> = 1500V; V <sub>BE</sub> = 0; T <sub>C</sub> =125°C			1.0 2.0	mA
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5.0V ; I <sub>C</sub> = 0			10	mA
h <sub>FE-1</sub>	DC Current Gain	Ic= 0.1A ; Vce= 5V	6		30	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4.5A ; V <sub>CE</sub> = 5V	2.25			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 0.1MHz		125		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V; f <sub>test</sub> = 1.0MHz		7		MHz

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